ELSEVIER

Journal of Crystal Growth 163 (1995) 478–481

JOURNAL OF CRYSTAL GROWTH

Author index

Akao, M., see Ito 163 (1996) 311
Akasaki, I. and H. Amano, Crystal growth of column-III nitride semiconductors and their electrical and optical properties 163 (1996) 86
Albrecht, J.H. Werner annd M., see Kühnle 163 (1996) 470
Alvarez, J.C., see Harada 163 (1996) 31
Amano, H., see Akasaki 163 (1996) 86
Anderson, D.M., M.G. Worster and S.H. Davis, The case for a dynamic contact angle in containerless solidification 163 (1996) 329
Anselmo, A., J. Koziol and V. Prasad, Full-scale experiments on solid-pellets feed continuous Czochralski growth of silicon crystals 163 (1996) 359
Aoki, H., see Ito 163 (1996) 311
Arias, J.M., see González-Muñoz 163 (1996) 434
Arima, Y., see Irisawa 163 (1996) 22
Aspnes, D.E., see Kamiya 163 (1996) 67

Bach, H., see Brinkmann 163 (1996) 369
Balakrishna, V., see Singh 163 (1996) 398
Banhart, F., see Zwanger 163 (1996) 445
Barata, P.A. and M.L. Serrano, Salting-out precipitation of potassium dihydrogen phosphate (KDP). II. Influence of agitation intensity 163 (1996) 426
Beatty, K.M., see Jackson 163 (1996) 461
Ben Omar, N., see González-Muñoz 163 (1996) 434
Bergmann, R., see Kühnle 163 (1996) 470
Biefeld, R.M., H.C. Chui, B.E. Hammons, W.G. Breiland, T.M. Brennan, E.D. Jones, M.H. Kim, P. Grodzinski, K.H. Chang and H.C. Lee, High purity GaAs and AlGaAs grown using tertiarybutylarsine, trimethylalumium, and trimethylgallium 163 (1996) 212
Bongers, M.M.G., see Li 163 (1996) 195
Breiland, W.G., see Biefeld 163 (1996) 212
Brennan, S., see Kisker 163 (1996) 54
Brennan, S., see Kamiya 163 (1996) 67
Brennan, T.M., see Biefeld 163 (1996) 212
Brinkmann, M., T. Rex, H. Bach and K. Westerholt, Crystal growth of high-T_C superconductors $Pr_{2-x}Ce_xCuO_{4+\delta}$ with substitutions of Ni and Co for Cu 163 (1996) 369

Cao, J.Y., see Li 163 (1996) 348
Chang, K.H., see Biefeld 163 (1996) 212
Chen, C.T., see Hu 163 (1996) 266
Chen, X.Q., see Li 163 (1996) 348
Cheng, H., see Li 163 (1996) 339
Cherkashina, N.V., see Volkov 163 (1996) 377
Christoffersen, J., M.R. Christoffersen and T. Johansen, Kinetics of growth and dissolution of fluorapatite 163 (1996) 295
Christoffersen, J., M.R. Christoffersen and T. Johansen, Some new aspects of surface nucleation applied to the growth and dissolution of fluorapatite and hydroxyapatite 163 (1996) 304
Christoffersen, M.R., see Christoffersen 163 (1996) 295
Christoffersen, M.R., see Christoffersen 163 (1996) 304
Chu, J.H., see Li 163 (1996) 348
Chui, H.C., see Biefeld 163 (1996) 212
Chung, Hyung-Tae, Seung-Cheol Lee and Jong-Kyu Yoon, Numerical prediction of operational parameters in Czochralski growth of large-scale Si 163 (1996) 249
Chuvilin, A.L., see Volkov 163 (1996) 377
Cui, Q., see Li 163 (1996) 339
Cui, S.F., see Li 163 (1996) 339

Dao Thi, M.H., see Lisgarten 163 (1996) 474
Dash, J.G., see Ishizaki 163 (1996) 455
Davis, R.F., S. Tanaka and R.C. Kern, Microstructural evolution and defect formation during the initial stages of the growth of silicon carbide and aluminum nitride on α(6H)-SiC(0001) substrates 163 (1996) 93
Davis, S.H., see Anderson 163 (1996) 329
Dong, C., see Li 163 (1996) 339
Dong, H.K., see Tu 163 (1996) 187

Eguchi, M., see Kakimoto 163 (1996) 238

Feng, Q., see Yanagisawa 163 (1996) 285
Fernelius, N., see Singh 163 (1996) 398
Fukuda, T., see Shimamura 163 (1996) 388
Fukuda, T., see Kimura 163 (1996) 393
Fuoss, P.H., see Kisker 163 (1996) 54
Fuoss, P.H., see Kamiya 163 (1996) 67
Furukawa, Y., see Ishizaki 163 (1996) 455

Gallagher, H.G., see Wang 163 (1996) 272

ELSEVIER

Journal of Crystal Growth 163 (1995) 478–481

JOURNAL OF CRYSTAL GROWTH

Author index

Akao, M., see Ito 163 (1996) 311
Akasaki, I. and H. Amano, Crystal growth of column-III nitride semiconductors and their electrical and optical properties 163 (1996) 86
Albrecht, J.H. Werner annd M., see Kühnle 163 (1996) 470
Alvarez, J.C., see Harada 163 (1996) 31
Amano, H., see Akasaki 163 (1996) 86
Anderson, D.M., M.G. Worster and S.H. Davis, The case for a dynamic contact angle in containerless solidification 163 (1996) 329
Anselmo, A., J. Koziol and V. Prasad, Full-scale experiments on solid-pellets feed continuous Czochralski growth of silicon crystals 163 (1996) 359
Aoki, H., see Ito 163 (1996) 311
Arias, J.M., see González-Muñoz 163 (1996) 434
Arima, Y., see Irisawa 163 (1996) 22
Aspnes, D.E., see Kamiya 163 (1996) 67

Bach, H., see Brinkmann 163 (1996) 369
Balakrishna, V., see Singh 163 (1996) 398
Banhart, F., see Zwanger 163 (1996) 445
Barata, P.A. and M.L. Serrano, Salting-out precipitation of potassium dihydrogen phosphate (KDP). II. Influence of agitation intensity 163 (1996) 426
Beatty, K.M., see Jackson 163 (1996) 461
Ben Omar, N., see González-Muñoz 163 (1996) 434
Bergmann, R., see Kühnle 163 (1996) 470
Biefeld, R.M., H.C. Chui, B.E. Hammons, W.G. Breiland, T.M. Brennan, E.D. Jones, M.H. Kim, P. Grodzinski, K.H. Chang and H.C. Lee, High purity GaAs and AlGaAs grown using tertiarybutylarsine, trimethylalumium, and trimethylgallium 163 (1996) 212
Bongers, M.M.G., see Li 163 (1996) 195
Breiland, W.G., see Biefeld 163 (1996) 212
Brennan, S., see Kisker 163 (1996) 54
Brennan, S., see Kamiya 163 (1996) 67
Brennan, T.M., see Biefeld 163 (1996) 212
Brinkmann, M., T. Rex, H. Bach and K. Westerholt, Crystal growth of high-T_C superconductors $Pr_{2-x}Ce_xCuO_{4+\delta}$ with substitutions of Ni and Co for Cu 163 (1996) 369

Cao, J.Y., see Li 163 (1996) 348
Chang, K.H., see Biefeld 163 (1996) 212
Chen, C.T., see Hu 163 (1996) 266
Chen, X.Q., see Li 163 (1996) 348
Cheng, H., see Li 163 (1996) 339
Cherkashina, N.V., see Volkov 163 (1996) 377
Christoffersen, J., M.R. Christoffersen and T. Johansen, Kinetics of growth and dissolution of fluorapatite 163 (1996) 295
Christoffersen, J., M.R. Christoffersen and T. Johansen, Some new aspects of surface nucleation applied to the growth and dissolution of fluorapatite and hydroxyapatite 163 (1996) 304
Christoffersen, M.R., see Christoffersen 163 (1996) 295
Christoffersen, M.R., see Christoffersen 163 (1996) 304
Chu, J.H., see Li 163 (1996) 348
Chui, H.C., see Biefeld 163 (1996) 212
Chung, Hyung-Tae, Seung-Cheol Lee and Jong-Kyu Yoon, Numerical prediction of operational parameters in Czochralski growth of large-scale Si 163 (1996) 249
Chuvilin, A.L., see Volkov 163 (1996) 377
Cui, Q., see Li 163 (1996) 339
Cui, S.F., see Li 163 (1996) 339

Dao Thi, M.H., see Lisgarten 163 (1996) 474
Dash, J.G., see Ishizaki 163 (1996) 455
Davis, R.F., S. Tanaka and R.C. Kern, Microstructural evolution and defect formation during the initial stages of the growth of silicon carbide and aluminum nitride on α(6H)-SiC(0001) substrates 163 (1996) 93
Davis, S.H., see Anderson 163 (1996) 329
Dong, C., see Li 163 (1996) 339
Dong, H.K., see Tu 163 (1996) 187

Eguchi, M., see Kakimoto 163 (1996) 238

Feng, Q., see Yanagisawa 163 (1996) 285
Fernelius, N., see Singh 163 (1996) 398
Fukuda, T., see Shimamura 163 (1996) 388
Fukuda, T., see Kimura 163 (1996) 393
Fuoss, P.H., see Kisker 163 (1996) 54
Fuoss, P.H., see Kamiya 163 (1996) 67
Furukawa, Y., see Ishizaki 163 (1996) 455

Gallagher, H.G., see Wang 163 (1996) 272

Garside, J., see Taguchi 163 (1996) 318
Giling, L.J., see Li 163 (1996) 195
Giling, L.J., see Li 163 (1996) 203
Gilmer, G.H., see Jackson 163 (1996) 461
González-Muñoz, M.T., N. Ben Omar, M. Martínez-Cañamero, M. Rodríguez-Gallego, A. López Galindo and J.M. Arias, Struvite and calcite crystallization induced by cellular membranes of *Myxococcus xanthus* 163 (1996) 434
Grodzinski, P., see Biefeld 163 (1996) 212

Hamakawa, E., see Hayakawa 163 (1996) 220
Hammons, B.E., see Biefeld 163 (1996) 212
Han, T.P.J., see Wang 163 (1996) 272
Han, Y., see Hu 163 (1996) 266
Harada, J., I. Takahashi, Y. Itoh, N.S. Sokolov, N.L. Yakovlev, Y. Shusterman and J.C. Alvarez, X-ray scattering from surfaces and interfaces and its application to the characterization of CaF_2/Si(111) interfaces 163 (1996) 31
Hatta, K., M. Higuchi, J. Takahashi and K. Kodaira, Floating zone growth and characterization of aluminum-doped rutile single crystals 163 (1996) 279
Hayakawa, Y., E. Hamakawa, T. Koyama and M. Kumagawa, Rapid diffusion of Ga into InSb and precipitation of In 163 (1996) 220
Henderson, B., see Wang 163 (1996) 272
Henningsen, T., see Singh 163 (1996) 398
Higuchi, M., see Hatta 163 (1996) 279
Hiruma, K., H. Murakoshi, M. Yazawa and T. Katsuyama, Self-organized growth of GaAs/InAs heterostructure nanocylinders by organometallic vapor phase epitaxy 163 (1996) 226
Hopkins, F.K., see Singh 163 (1996) 398
Hotta, Y., see Tsutsui 163 (1996) 440
Hu, X.B., S.S. Jiang, X.R. Huang, W. Zeng, W.J. Liu, C.T. Chen, Q.L. Zhao, J.H. Jiang, Z.G. Wang, Y.L. Tian and Y. Han, The formation mechanisms of dislocations and negative crystals in LiB_3O_5 single crystals 163 (1996) 266
Huang, J.-W., see Kuech 163 (1996) 171
Huang, X.R., see Hu 163 (1996) 266

Ichimiya, A., H. Nakahara and Y. Tanaka, Atomic structures of Si(111) surface during silicon epitaxial growth 163 (1996) 39
Inoue, T., see Takemoto 163 (1996) 100
Ioku, K., see Yanagisawa 163 (1996) 285
Irisawa, T. and Y. Arima, Structural feature of surface in MBE growth Monte Carlo simulation 163 (1996) 22
Ishizaki, T., M. Maruyama, Y. Furukawa and J.G. Dash, Premelting of ice in porous silica glass 163 (1996) 455
Ito, A., S. Nakamura, H. Aoki, M. Akao, K. Teraoka, S. Tsutsumi, K. Onuma and T. Tateishi, Hydrothermal growth of carbonate-containing hydroxyapatite single crystals 163 (1996) 311
Itoh, O., see Nugraha 163 (1996) 353
Itoh, Y., see Harada 163 (1996) 31

Jackson, K.A., G.H. Gilmer, D.E. Temkin and K.M. Beatty, Microsegregation far from equilibrium 163 (1996) 461
Jiang, J.H., see Hu 163 (1996) 266
Jiang, S.S., see Hu 163 (1996) 266
Jimbo, T., see Soga 163 (1996) 165
Johansen, T., see Christoffersen 163 (1996) 295
Johansen, T., see Christoffersen 163 (1996) 304
Jones, E.D., see Biefeld 163 (1996) 212

Kakimoto, K., K.-W. Yi and M. Eguchi, Oxygen transfer during single silicon crystal growth in Czochralski system with vertical magnetic fields 163 (1996) 238
Kamiya, I., L. Mantese, D.E. Aspnes, D.W. Kisker, P.H. Fuoss, G.B. Stephenson and S. Brennan, Optical characterization of surfaces during epitaxial growth using RDS and GIXS 163 (1996) 67
Katsuyama, T., see Hiruma 163 (1996) 226
Kern, R.C., see Davis 163 (1996) 93
Key, D.L., see Lisgarten 163 (1996) 474
Khusnatdinov, N.N. and V.F. Petrenko, Fast-growth technique for ice single crystals 163 (1996) 420
Kim, M.H., see Biefeld 163 (1996) 212
Kimura, H., V.V. Kochurikhin, K. Shimamura and T. Fukuda, OH bands in $(Dy_{1-x}Gd_x)_3Ga_5O_{12}$, $Dy_3(Ga_{1-y}Al_y)_5O_{12}$ and related oxides grown by the Czochralski method 163 (1996) 393
Kishimoto, D., see Nishinaga 163 (1996) 60
Kisker, D.W., G.B. Stephenson, J. Tersoff, P.H. Fuoss and S. Brennan, Atomic scale studies of epitaxial growth processes using X-ray techniques 163 (1996) 54
Kisker, D.W., see Kamiya 163 (1996) 67
Kochurikhin, V.V., see Kimura 163 (1996) 393
Kodaira, K., see Hatta 163 (1996) 279
Kohno, T., see Shimamura 163 (1996) 388
Komatsu, H., see Takemoto 163 (1996) 100
Komura, T., see Yao 163 (1996) 78
Koukitu, A., N. Takahashi and H. Seki, In situ monitoring of the GaAs growth process in halogen transport atomic layer epitaxy 163 (1996) 180
Koyama, T., see Hayakawa 163 (1996) 220
Koziol, J., see Anselmo 163 (1996) 359
Kuech, T.F., S. Nayak, J.-W. Huang and J. Li, Chemical and physical effects in oxygen incorporation during the metalorganic vapor phase epitaxial growth of GaAs 163 (1996) 171
Kühnle, J., R. Bergmann, J.H. Werner annd M. Albrecht, Silicon surface passivation by metal layers for low-temperature epitaxy 163 (1996) 470

Kumagawa, M., see Hayakawa 163 (1996) 220
Kuwano, N. and K. Oki, Ising model analysis of the formation mechanism of ordered structures in III–V alloy semiconductors 163 (1996) 122
Kvit, A.V., see Volkov 163 (1996) 377

Lazzarini, L., see Li 163 (1996) 195
Lee, Ching-Ting, Jih-Hsien Yeh and Yen-Tang Lyu, Characterization of Nd-doped AsGaAs grown by liquid phase epitaxy 163 (1996) 343
Lee, H.C., see Biefeld 163 (1996) 212
Lee, Seung-Cheol, see Chung 163 (1996) 249
Li, Biao, J.H. Chu, J.Q. Zhu, X.Q. Chen, J.Y. Cao and D.Y. Tang, Morphology investigation of $Hg_{1-x}Cd_xTe$ liquid phase epitaxial films 163 (1996) 348
Li, J., see Kuech 163 (1996) 171
Li, Ming, S.F. Cui, C. Dong, H. Cheng, F. Wu, Q. Cui and Z.H. Mai, Replication of steps from substrate surface to superlattice interfaces 163 (1996) 339
Li, N.Y., see Tu 163 (1996) 187
Li, Y., G. Salviati, M.M.G. Bongers, L. Lazzarini, L. Nasi and L.J. Giling, On the formation of antiphase domains in the system of GaAs on Ge 163 (1996) 195
Li, Y. and L.J. Giling, A closer study on the self-annihilation of antiphase boundaries in GaAs epilayers 163 (1996) 203
Lisgarten, J.N., D. Maes, M.H. Dao Thi, L. Wyns, D.L. Key and J.A. Marks, Crystal orientation effect under microgravity conditions 163 (1996) 474
Liu, J. and R.H. Zee, Growth of molybdenum-based alloy single crystals using electron beam zone melting 163 (1996) 259
Liu, W.J., see Hu 163 (1996) 266
Liu, Xi, see Meng 163 (1996) 232
López Galindo, A., see González-Muñoz 163 (1996) 434
Louchev, O.A., Thermal effects and kinetics in step-flow crystal growth of α-HgI_2 163 (1996) 411
Lyu, Yen-Tang, see Lee 163 (1996) 343

Madhukar, A., A unified atomistic and kinetic framework for growth front morphology evolution and defect initiation in strained epitaxy 163 (1996) 149
Maes, D., see Lisgarten 163 (1996) 474
Mai, Z.H., see Li 163 (1996) 339
Maksimov, I.L., see Nishioka 163 (1996) 1
Mantese, L., see Kamiya 163 (1996) 67
Marks, J.A., see Lisgarten 163 (1996) 474
Martínez-Cañamero, M., see González-Muñoz 163 (1996) 434
Maruyama, M., see Ishizaki 163 (1996) 455
Meng, Guangyao, Xi Liu, Song Xie and Dingkun Peng, ⟨0001⟩-oriented growth of AlN films on Si(111) by microwave plasma CVD with $AlBr_3$–NH_3–N_2 system 163 (1996) 232
Minoda, H. and K. Yagi, In-situ observations of growths of Si and Ge on metal-adsorbed Si(111) surfaces by REM-RHEED 163 (1996) 48
Miyashita, S., see Takemoto 163 (1996) 100
Moiseev, I.I., see Volkov 163 (1996) 377
Murakoshi, H., see Hiruma 163 (1996) 226

Nakahara, H., see Ichimiya 163 (1996) 39
Nakamura, S., see Ito 163 (1996) 311
Nakayama, H., T. Takeguchi and T. Nishino, Atom correlation and configurational ordering in pseudobinary epitaxial semiconductors 163 (1996) 135
Nasi, L., see Li 163 (1996) 195
Nayak, S., see Kuech 163 (1996) 171
Nishinaga, T., X.Q. Shen and D. Kishimoto, Surface diffusion length of cation incorporation studies by microprobe-RHEED/SEM MBE 163 (1996) 60
Nishino, T., see Nakayama 163 (1996) 135
Nishioka, K. and I.L. Maksimov, Reconsideration of the concept of critical nucleus and the Gibbs–Thomson equation 163 (1996) 1
Nishizawa, J., see Nugraha 163 (1996) 353
Novotortsev, V.M., see Volkov 163 (1996) 377
Nugraha, O. Itoh, K. Suto and J. Nishizawa, Growth and electrical properties of PbTe epitaxial layers grown by temperature difference method under controlled vapor pressure liquid phase epitaxy 163 (1996) 353

Oki, K., see Kuwano 163 (1996) 122
Onuma, K., see Ito 163 (1996) 311

Peng, Dingkun, see Meng 163 (1996) 232
Petrenko, V.F., see Khusnatdinov 163 (1996) 420
Prasad, V., see Anselmo 163 (1996) 359

Rex, T., see Brinkmann 163 (1996) 369
Rodríguez-Gallego, M., see González-Muñoz 163 (1996) 434

Salviati, G., see Li 163 (1996) 195
Sasaki, A., Atomic scale study of InAs/GaAs heteroepitaxy 163 (1996) 143
Sato, K., see Tsutsui 163 (1996) 440
Schröder, W., see Wollweber 163 (1996) 243
Schulz, D., see Wollweber 163 (1996) 243
Seeger, A., see Zwanger 163 (1996) 445
Seki, H., see Koukitu 163 (1996) 180
Serrano, M.L., see Barata 163 (1996) 426
Shen, X.Q., see Nishinaga 163 (1996) 60
Shimamura, K., H. Takeda, T. Kohno and T. Fukuda, Growth and characterization of lanthanum gallium silicate $La_3Ga_5SiO_{14}$ single crystals for piezoelectric applications 163 (1996) 388
Shimamura, K., see Kimura 163 (1996) 393
Shusterman, Y., see Harada 163 (1996) 31

Singh, N.B., T. Henningsen, V. Balakrishna, D.R. Suhre, N. Fernelius, F.K. Hopkins and D.E. Zelmon, Growth and characterization of gallium selenide crystals for far-infrared conversion applications 163 (1996) 398
Soga, T., T. Jimbo and M. Umeno, Initial stage of GaP/Si heteroepitaxial growth by metalorganic chemical vapor deposition 163 (1996) 165
Sokolov, N.S., see Harada 163 (1996) 31
Stephenson, G.B., see Kisker 163 (1996) 54
Stephenson, G.B., see Kamiya 163 (1996) 67
Stringfellow, G.B. and L.C. Su, Step structure during OMVPE growth of ordered GaInP 163 (1996) 128
Su, L.C., see Stringfellow 163 (1996) 128
Suhre, D.R., see Singh 163 (1996) 398
Suto, K., see Nugraha 163 (1996) 353
Suzuki, T., Oxygen partial pressure dependence of optical absorption in lithium niobate 163 (1996) 403

Taguchi, K., J. Garside and N.S. Tavare, Nucleation and growth kinetics of barium sulphate in batch precipitation 163 (1996) 318
Takahashi, I., see Harada 163 (1996) 31
Takahashi, J., see Hatta 163 (1996) 279
Takahashi, N., see Koukitu 163 (1996) 180
Takeda, H., see Shimamura 163 (1996) 388
Takeguchi, T., see Nakayama 163 (1996) 135
Takemoto, J., S. Miyashita, T. Inoue and H. Komatsu, Liquid phase epitaxial growth of bismuth based superconductors 163 (1996) 100
Tanaka, S., see Davis 163 (1996) 93
Tanaka, Y., see Ichimiya 163 (1996) 39
Tang, D.Y., see Li 163 (1996) 348
Tateishi, T., see Ito 163 (1996) 311
Tavare, N.S., see Taguchi 163 (1996) 318
Temkin, D.E., see Jackson 163 (1996) 461
Teraoka, K., see Ito 163 (1996) 311
Tersoff, J., see Kisker 163 (1996) 54
Tian, Y.L., see Hu 163 (1996) 266
Tsirkov, G.A., see Volkov 163 (1996) 377
Tsutsui, K., Y. Hotta and K. Sato, Melt crystallization of behenic acid in microspheres dispersed in polymer 163 (1996) 440
Tsutsumi, S., see Ito 163 (1996) 311
Tu, C.W., H.K. Dong and N.Y. Li, Growth, etching, doping and effects of Ar^+ laser irradiation in chemical beam epitaxy of GaAs with novel precursors 163 (1996) 187

Uesugi, K., see Yao 163 (1996) 78
Umeno, M., see Soga 163 (1996) 165

Van Tendeloo, G., see Volkov 163 (1996) 377
Vargaftik, M.N., see Volkov 163 (1996) 377
Volkov, V.V., G. Van Tendeloo, G.A. Tsirkov, N.V. Cherkashina, M.N. Vargaftik, I.I. Moiseev, V.M. Novotortsev, A.V. Kvit and A.L. Chuvilin, Long- and short-distance ordering of the metal cores of giant Pd clusters 163 (1996) 377

Wang, G., H.G. Gallagher, T.P.J. Han and B. Henderson, The growth and optical assessment of Cr^{3+}-doped $RX(BO_3)_4$ crystals with R = Y, Gd; X = Al, Sc 163 (1996) 272
Wang, Z.G., see Hu 163 (1996) 266
Westerholt, K., see Brinkmann 163 (1996) 369
Wollweber, J., D. Schulz and W. Schröder, Si_xGe_{1-x} single crystals grown by the RF-heated float zone technique 163 (1996) 243
Worster, M.G., see Anderson 163 (1996) 329
Wu, F., see Li 163 (1996) 339
Wyns, L., see Lisgarten 163 (1996) 474

Xie, Song, see Meng 163 (1996) 232

Yagi, K., see Minoda 163 (1996) 48
Yakovlev, N.L., see Harada 163 (1996) 31
Yamasaki, N., see Yanagisawa 163 (1996) 285
Yanagisawa, K., Q. Feng, K. Ioku and N. Yamasaki, Hydrothermal single crystal growth of calcite in ammonium acetate solution 163 (1996) 285
Yao, T., K. Uesugi, T. Komura and M. Yoshimura, Atomistic study on solid phase epitaxy processes on Si(100) surfaces by the scanning tunneling microscope 163 (1996) 78
Yasuda, Y., see Zaima 163 (1996) 105
Yazawa, M., see Hiruma 163 (1996) 226
Yeh, Jih-Hsien, see Lee 163 (1996) 343
Yi, K.-W., see Kakimoto 163 (1996) 238
Yoon, Jong-Kyu, see Chung 163 (1996) 249
Yoshimura, M., see Yao 163 (1996) 78

Zaima, S. and Y. Yasuda, Studies on the suppression of Ge segregation during Si overgrowth on Ge(n ML)/Si(100) substrates by gas-source MBE 163 (1996) 105
Zangwill, A., Some causes and a consequence of epitaxial roughening 163 (1996) 8
Zee, R.H., see Liu 163 (1996) 259
Zelmon, D.E., see Singh 163 (1996) 398
Zeng, W., see Hu 163 (1996) 266
Zhang, S.B. and A. Zunger, Predicted structures and stabilities of the surface A grooves and double bilayer height steps on the GaAs(001)-2 × 4 surface 163 (1996) 113
Zhao, Q.L., see Hu 163 (1996) 266
Zhu, J.Q., see Li 163 (1996) 348
Zunger, A., see Zhang 163 (1996) 113
Zwanger, M.S., F. Banhart and A. Seeger, Formation and delay of spherical concentric-shell carbon clusters 163 (1996) 445

ELSEVIER

Journal of Crystal Growth 163 (1996) 482–483

JOURNAL OF CRYSTAL GROWTH

Subject index

Aluminum
– gallium arsenide 343
– nitride 93, 232
Apparatus
– for high T_c crystals 369
– for fast growth of ice 420
– for large single crystals of bone and tooth mineral 311

Barium
– sulphide 318

Calcium
– fluoride 31
Computer simulation
– of front growth morphology 149
– of segregation 461
– of temperature distribution 238
Convection 420
Copper
– II oxalate 474

Device characterization
– electronic materials 212
– lasers 272, 398
– piezoelectric bulk acoustic wave 388
Diffusional control
– of cation incorporation 60

Electronic materials, see Device characterization
Epitaxy, see Thin film growth

Fullerene 445

Gallium
– arsenide 54, 60, 149, 171, 180, 187, 195, 203, 212, 226
– indium arsenide 149
– indium phosphide 128
– phosphide 165
– selenide 398
Germanium 48, 105

Hydrodynamics, see Convection

Ice 420, 455
Indium
– arsenide 60, 143, 226
– gallium antimonide 220

Kinetics
– of dissolution 295, 304
– of growth 54, 60, 143, 149, 232, 295, 304, 318, 411, 420, 445, 461
– of interface control 86, 149
– of nucleation 54, 67, 426, 440

Lasers, see Device characterization
Lead
– telluride 353

Melt growth technique
– by Bridgman–Stockbarger method
– – of gallium selenide 398
– – of indium gallium antimonide 220
– by Czochralski method
– – of dysprosium gadolinium gallium garnet 393
– – of dysprosium gallium aluminum garnet 393
– – of lanthanum gallium silicate 388
– – of lithium niobate 403
– – of silicon 238, 359
– – theory of large scale growth 249
– by floating zone method
– – of aluminum doped rutile 279
– – of molybdenum alloys 259
– by zone melting
– – of silicon germanium 243
– theory
– – of dynamic contact angle 329
– – of microsegregation 461
Mercury
– cadmium telluride 348
– iodide 411
Microgravity, growth under
– of copper two oxalate 474
– theory of dynamic contact angle 329
Monte Carlo simulation
– of ordered structure 122
Morphological stability
– of fullerene 445
– of mercury cadmium telluride 348

Nucleation
– of barium sulphide 318
– of behenic acid 440

– of calcite 434
– of potassium dihydrogen phosphate 426
– of struvite 434
– theory of
– – critical nucleus 1

Phase diagram
– of indium gallium antimonide 220
– of ternary borates 272
Precursor
– for gallium aluminum arsenide 212
– for gallium arsenide 187, 212
– for fullerene formation 445

Silicon 39, 48, 78, 105, 238, 359
– germanium 243
Solid growth technique
– by ion irradiation
– – of silicon 78
Solution growth technique
– by bacterial membranes
– – of struvite 434
– by flux method
– – of gadolinium aluminum borate 272
– – of gadolinium scandium borate 272
– – of lithium triborate 266
– – of ytterbium aluminum borate 272
– – of ytterbium scandium borate 272
– by hydrothermal growth
– – of calcite 285
– – of hydroxy apatite 311
– by low temperature method
– – of behenic acid 440
– – of palladium clusters 377
– – of silicon 470
– theory of supersaturation 318
Stefan problem or moving boundary
– of dynamic contact angle 329
Superconductivity materials, high T_c
– bulk
– – of praseodymium cerium copper oxide 369
– film
– – of BSCCO 100
– – of BSCO 100
Superlattices, multilayers
– of III–V compounds 226
Surface energy, determination
– of fluorapatite 295, 304
– of hydroxyapatite 304
Surface morphology
– of calcium fluoride 31
– of gallium arsenide 171
– of germanium 48
Surface structure
– of gallium arsenide 54, 67, 113, 180
– of ice 455
– of molecular beam epitaxy 22
– of replicated substrate surface 339
– of silicon 78
– theory of roughening 8

Thin film growth, epitaxy
– by atomic layer epitaxy
– – of calcium fluoride 31
– – of gallium arsenide 180
– by chemical beam epitaxy
– – of gallium arsenide 187
– by gas source molecular beam epitaxy
– – of germanium 105
– – of silicon 105
– by liquid phase epitaxy
– – of BSCCO 100
– – of BSCO 100
– – of lead telluride 353
– – of mercury cadmium telluride 348
– – of neodymium doped aluminum gallium arsenide 343
– – of silicon 470
– by molecular beam epitaxy
– – of aluminum gallium arsenide 149
– – of aluminum nitride 93
– – of calcium fluoride 31
– – of gallium arsenide 60, 149
– – of indium arsenide 60, 143, 149
– – of indium gallium arsenide 149
– – of silicon 39
– – of silicon carbide 93
– – theory of binary growth 135
– by vapor phase epitaxy
– – through evaporation and condensation
– – – of germanium 48
– – – of silicon 48
– – through metalorganic chemical vapor deposition
– – – of aluminum gallium arsenide 212
– – – of gallium aluminum nitride 86
– – – of gallium arsenide 54, 67, 171, 195, 203, 212
– – – of gallium indium nitride 86
– – – of gallium indium phosphide 128
– – – of gallium nitride 86
– – – of gallium phosphide 165
– – – theory of 54
– – through microwave plasma chemical vapor deposition
– – – of aluminum nitride 232

Vapor growth technique
– by evaporation and condensation
– – of alpha mercuric iodide 411
– – theory of coupled step flow 411
– Vapor–liquid–solid growth
– of ice 420

Whisker growth
– of gallium arsenide 226
– of indium arsenide 226